

L Number	Hits	Sear h Text	DB	Time stamp
1	1239	438/690,691,692.ccls.	USPAT	2002/06/17 12:18
2	971	438/623,624.ccls.	USPAT	2002/06/17 12:19
3	295	438/626.ccls.	USPAT	2002/06/17 12:19
4	248	438/715,716.ccls.	USPAT	2002/06/17 12:19
5	1	leong-lup\$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/17 12:19
6	23600	planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)	USPAT	2002/06/17 12:26
7	5156	(planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)) and (planar\$8 same heat\$3)	USPAT	2002/06/17 12:24
8	3442	((planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)) and (planar\$8 same heat\$3)) and (planar\$8 same (layer film wafer substrate))	USPAT	2002/06/17 12:25
9	1288	((planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)) and (planar\$8 same heat\$3)) and (planar\$8 same (layer film wafer substrate))) and (planar\$8 same mechan\$4)	USPAT	2002/06/17 12:28
10	58	planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)	EPO; JPO; DERWENT; IBM_TDB	2002/06/17 12:27
11	2248	planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)	US-PGPUB	2002/06/17 12:27
12	467	(planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)) and (planar\$8 same heat\$3)	US-PGPUB	2002/06/17 12:27
13	727	((((planar\$8 and heat\$3 and pressure and mechan\$4 and (layer film wafer substrate)) and (planar\$8 same heat\$3)) and (planar\$8 same (layer film wafer substrate))) and (planar\$8 same mechan\$4)) and (planar\$8 same pressure)	USPAT	2002/06/17 12:29